

	Type	Ref #	Hits	Search Text
16	IS&R	S16	539	(257/667).CCLS.
17	IS&R	S18	2899	(257/690,693).CCLS.
18	IS&R	S19	2	("5376816").PN.
19	IS&R	S20	2	("5899714").PN.
20	IS&R	S17	2400	(257/678).CCLS.
21	IS&R	S21	3537	(257/787).CCLS.
22	IS&R	S22	12	((("6121675") or ("6266197") or ("6342406") or ("6384472") or ("6492699") or ("4957882"))).PN.
23	IS&R	S23	2	("20030001210").PN.
24	IS&R	S24	2	("6762480").PN.
25	IS&R	S25	2	("20020145137").PN.
26	BRS	S27	70	((Heterojunction adj bipolar adj transistor) or (HBT)) and ((GaAsSb or gallium adj arsenide adj antimonide) with base)
27	BRS	S28	70	((Heterojunction adj bipolar adj transistor) or (HBT)) and ((GaAsSb or (gallium adj arsenide adj antimonide) or (arsenide adj gallium adj antimonide)) with base)
28	BRS	S26	98	((Heterojunction adj bipolar adj transistor) or (HBT)) and (GaAsSb or gallium adj arsenide adj antimonide)

N/A

	DBs	Time Stamp	Comments	Error Definition
16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 13:49		
17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 15:10		
18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 14:33		
19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 14:33		
20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 14:56		
21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 16:08		
22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 17:32		
23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/06 17:42		
24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 11:18		
25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 11:28		
26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 11:36		
27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 15:44		
28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 14:14		

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	Type	Ref #	Hits	Search Text
29	BRS	S29	66	((Heterojunction adj bipolar adj transistor) or (HBT)) and (GaAsSb or gallium adj arsenide adj antimonide) and (nm or micron or nanometer\$1)
30	BRS	S30	46	((Heterojunction adj bipolar adj transistor) or (HBT)) and (GaAsSb or gallium adj arsenide adj antimonide) and (base with (nm or micron or nanometer\$1))
31	BRS	S31	46	((Heterojunction adj bipolar adj transistor) or (HBT)) and (Ga\$4As\$4Sb or gallium adj arsenide adj antimonide) and (base with (nm or micron or nanometer\$1))
32	BRS	S32	46	((Heterojunction adj bipolar adj transistor) or (HBT)) and (Ga\$6As\$6Sb or gallium adj arsenide adj antimonide) and (base with (nm or micron or nanometer\$1))
33	BRS	S33	46	((Heterojunction adj bipolar adj transistor) or (HBT)) and (Ga\$6As\$6Sb or gallium adj arsenide adj antimonide) and (base with (nm or micron\$1 or nanometer\$1))
34	BRS	S34	46	((Heterojunction adj bipolar adj transistor) or (HBT)) and (Ga\$6As\$6Sb or gallium adj arsenide adj antimonide) and (base with (nm or micron\$1 or nanometer\$1 or mu))
35	BRS	S35	66524	"257"/\$.ccls. and ((Ga\$6As\$6Sb\$6 or As\$6Ga\$6Sb\$6 or (gallium adj arsenide adj antimonide) or (arsenide adj gallium adj antimonide)) samew base)
36	BRS	S36	80	"257"/\$.ccls. and ((Ga\$6As\$6Sb\$6 or As\$6Ga\$6Sb\$6 or (gallium adj arsenide adj antimonide) or (arsenide adj gallium adj antimonide)) same base)
37	BRS	S37	41	"257"/197-198.ccls. and ((Ga\$6As\$6Sb\$6 or As\$6Ga\$6Sb\$6 or (gallium adj arsenide adj antimonide) or (arsenide adj gallium adj antimonide)) same base)

	DBs	Time Stamp	Comments	Error Definition
29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 14:45		
30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 14:46		
31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 14:48		
32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 14:48		
33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 15:42		
34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 15:42		
35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 15:45		
36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 15:45		
37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 16:06		

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	Type	Ref #	Hits	Search Text
38	BRS	S38	58	"257"/\$.ccls. and ((Ga\$6As\$6Sb\$6 or As\$6Ga\$6Sb\$6 or (gallium adj arsenide adj antimonide) or (arsenide adj gallium adj antimonide)) same base) and ((heterojunction adj bipolar adj transistor or HBT))
39	BRS	S39	136	"257"/\$.ccls. and (Ga\$11Sb\$6 or (gallium adj arsenide adj antimonide) same base) and ((heterojunction adj bipolar adj transistor or HBT))
40	BRS	S40	58	"438"/\$.ccls. and (Ga\$11Sb\$6 or (gallium adj arsenide adj antimonide) same base) and ((heterojunction adj bipolar adj transistor or HBT))
41	IS&R	S41	2	("20020102848").PN.

	DBs	Time Stamp	Comments	Error Definition
38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 16:14		
39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/08 13:28		
40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/07 17:01		
41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/06/08 13:28		

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